



October 2005

FDZ291P

P-Channel 1.5 V Specified PowerTrench® BGA MOSFET

General Description

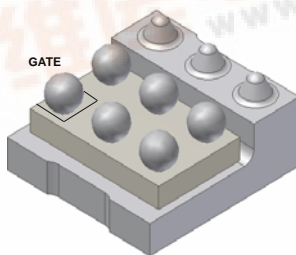
Combining Fairchild's advanced 1.5V specified PowerTrench process with state of the art BGA packaging, the FDZ291P minimizes both PCB space and $R_{DS(ON)}$. This BGA MOSFET embodies a breakthrough in packaging technology which enables the device to combine excellent thermal transfer characteristics, high current handling capability, ultra-low profile packaging, low gate charge, and low $R_{DS(ON)}$.

Applications

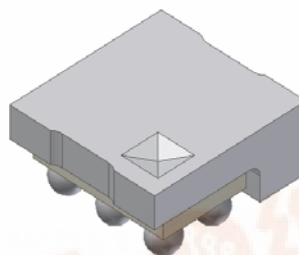
- Battery management
- Load switch
- Battery protection

Features

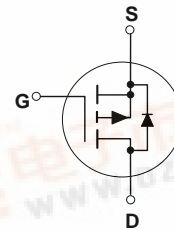
- -4.6 A, -20 V $R_{DS(ON)} = 40 \text{ m}\Omega @ V_{GS} = -4.5 \text{ V}$
 $R_{DS(ON)} = 60 \text{ m}\Omega @ V_{GS} = -2.5 \text{ V}$
 $R_{DS(ON)} = 160 \text{ m}\Omega @ V_{GS} = -1.5 \text{ V}$
- Occupies only 2.25 mm^2 of PCB area.
Less than 50% of the area of a SSOT-6
- Ultra-thin package: less than 0.85 mm height when mounted to PCB
- Outstanding thermal transfer characteristics:
4 times better than SSOT-6
- Ultra-low $Q_g \times R_{DS(ON)}$ figure-of-merit
- High power and current handling capability.



Bottom



Top



Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	-20	V
V_{GSS}	Gate-Source Voltage	± 8	V
I_D	Drain Current – Continuous (Note 1a)	-4.6	A
	– Pulsed	-10	
P_D	Power Dissipation for Single Operation (Note 1a)	1.7	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	72	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1a)	2	

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
D	FDZ291P	7"	8mm	3000 units



Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\text{ }\mu\text{A}$, Referenced to 25°C		-12		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
I_{GSS}	Gate–Body Leakage.	$V_{GS} = \pm 8\text{ V}, V_{DS} = 0\text{ V}$			± 100	nA

On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-0.4	-0.7	-1.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250\text{ }\mu\text{A}$, Referenced to 25°C		2		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = -4.5\text{ V}, I_D = -4.6\text{ A}$ $V_{GS} = -2.5\text{ V}, I_D = -3.6\text{ A}$ $V_{GS} = -1.5\text{ V}, I_D = -1.0\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -4.6\text{ A}, T_J = 125^\circ\text{C}$		31 43 85 42	40 60 160 55	m Ω
$I_{D(on)}$	On–State Drain Current	$V_{GS} = -4.5\text{ V}, V_{DS} = -5\text{ V}$	-10			A
g_{FS}	Forward Transconductance	$V_{DS} = -5\text{ V}, I_D = -4.6\text{ A}$		16		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		1010		pF
C_{oss}	Output Capacitance			160		pF
C_{rss}	Reverse Transfer Capacitance			80		pF

Switching Characteristics (Note 2)

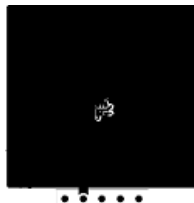
$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = -10\text{ V}, I_D = -1\text{ A},$ $V_{GS} = -4.5\text{ V}, R_{GEN} = 6\text{ }\Omega$		11	19	ns
t_r	Turn–On Rise Time			9	18	ns
$t_{d(off)}$	Turn–Off Delay Time			36	58	ns
t_f	Turn–Off Fall Time			16	29	ns
Q_g	Total Gate Charge	$V_{DS} = -10\text{ V}, I_D = -4.6\text{ A},$ $V_{GS} = -4.5\text{ V}$		9	13	nC
Q_{gs}	Gate–Source Charge			1.6		nC
Q_{gd}	Gate–Drain Charge			1.9		nC

Drain–Source Diode Characteristics and Maximum Ratings

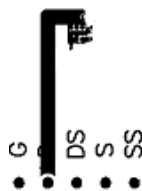
I _S	Maximum Continuous Drain–Source Diode Forward Current				–1.4	A
V _{SD}	Drain–Source Diode Forward Voltage	V _{GS} = 0V, I _S = –1.4 A (Note 2)		–0.7	–1.2	V
t _{rr}	Diode Reverse Recovery Time	I _F = –4.6 A, dI _F /dt = 100A/μs		17		ns
Q _{rr}	Diode Reverse Recovery Charge			5		nC

Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² 2 oz. copper pad on a 1.5 x 1.5 in. board of FR-4 material. The thermal resistance from the junction to the circuit board side of the solder ball, $R_{\theta JB}$, is defined for reference. For $R_{\theta JC}$, the thermal reference point for the case is defined as the top surface of the copper chip carrier. $R_{\theta JC}$ and $R_{\theta JB}$ are guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.



- a) $72^\circ\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper, 1.5" x 1.5" x 0.062" thick PCB



- b) $157^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%

Typical Characteristics

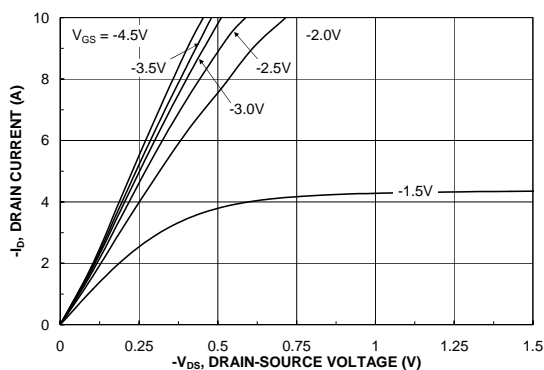


Figure 1. On-Region Characteristics.

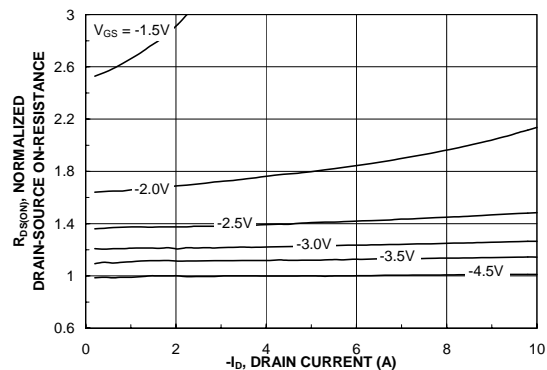


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

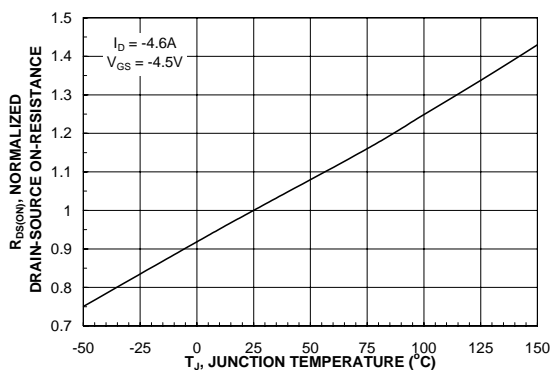


Figure 3. On-Resistance Variation with Temperature.

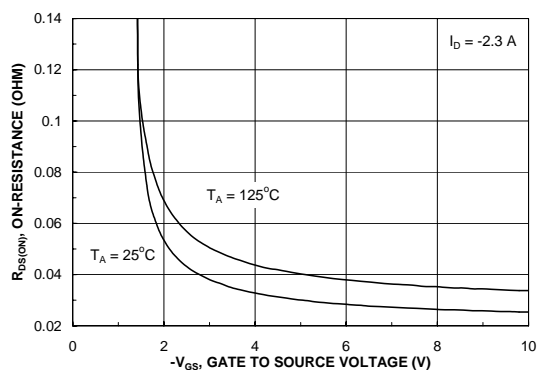


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

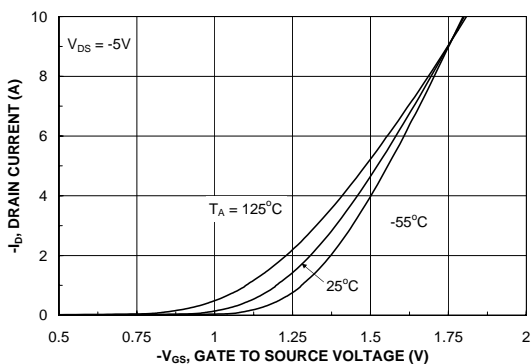


Figure 5. Transfer Characteristics.

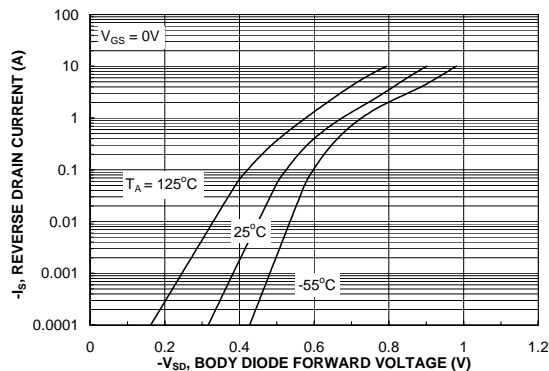


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

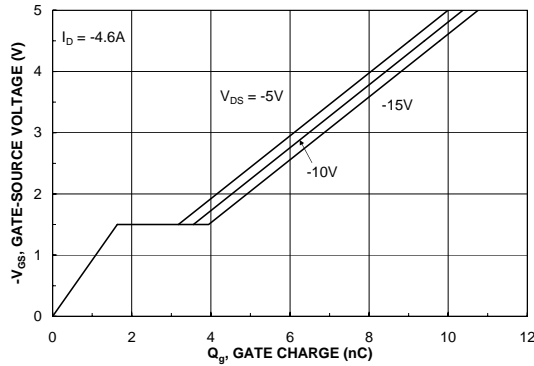


Figure 7. Gate Charge Characteristics.

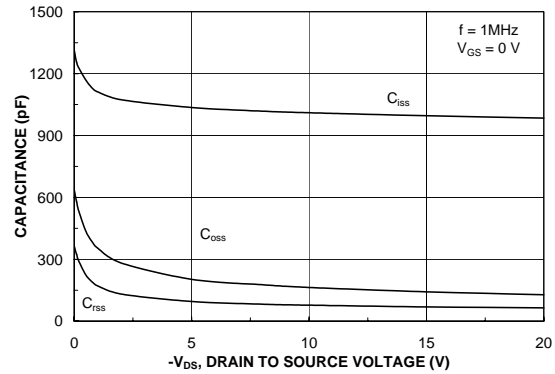


Figure 8. Capacitance Characteristics.

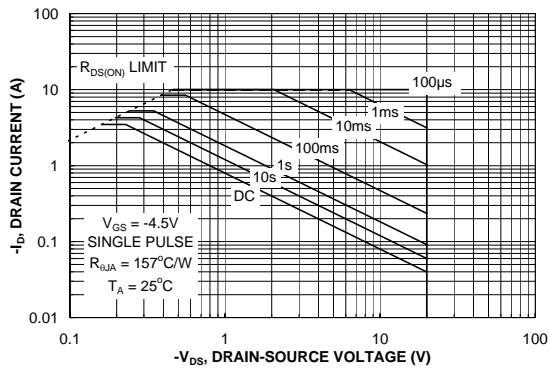


Figure 9. Maximum Safe Operating Area.

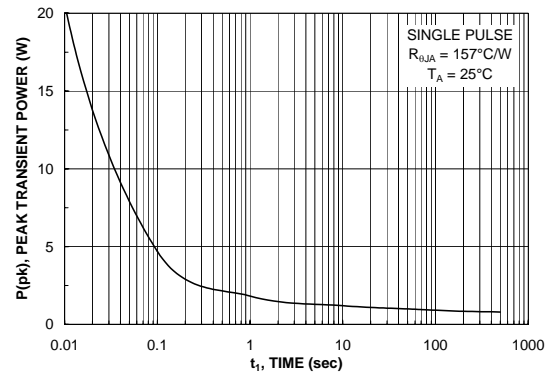


Figure 10. Single Pulse Maximum Power Dissipation.

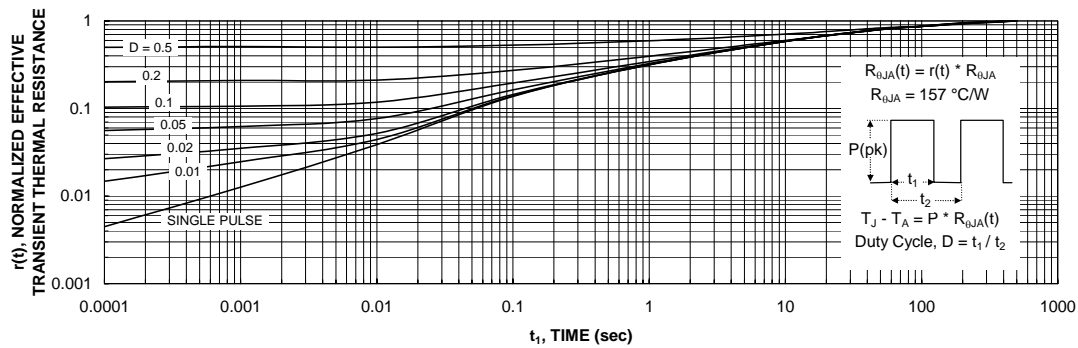
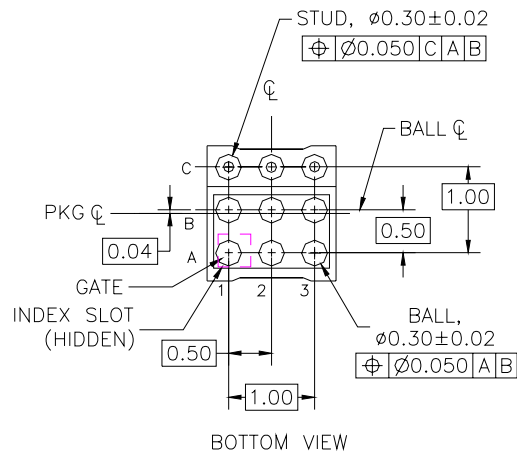
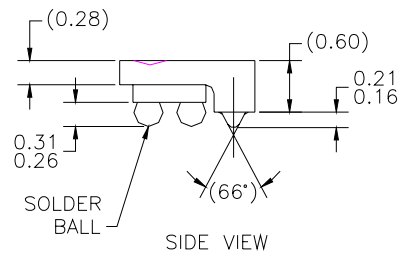
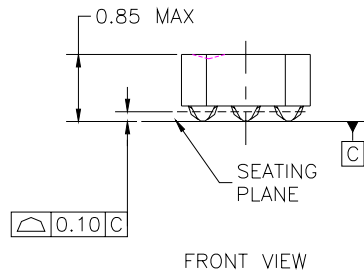
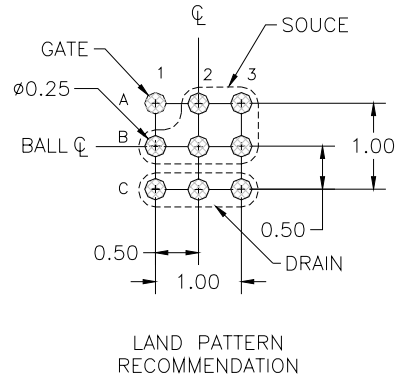
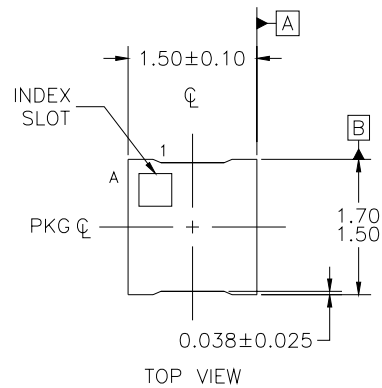


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b.
Transient thermal response will change depending on the circuit board design.

Dimensional Pad and Layout



NOTES: UNLESS OTHERWISE SPECIFIED

- A) ALL DIMENSIONS ARE IN MILLIMETERS.
- B) NO JEDEC REGISTRATION REFERENCE AS OF SEPTEMBER 2003.
- C) BALL/STUD CONFIGURATION TABLE

TERMINAL ID	DESIGNATION	TERMINAL TYPE
C1,C2,C3	DRAIN	COPPER STUD
A1	GATE	BALL
A2,A3,B1,B2,B3	SOURCE	BALL

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FACT Quiet Series TM		OPTOPLANAR TM	SPM TM	
Across the board. Around the world. TM		PACMAN TM	Stealth TM	
The Power Franchise [®]		POP TM	SuperFET TM	
Programmable Active Droop TM		Power247 TM	SuperSOT TM -3	
		PowerEdge TM	SuperSOT TM -6	

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